

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Gehrke, Thomas

Serial Number: Not Assigned

Filed: Concurrently Herewith

For: PENDEOEPIITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE
SEMICONDUCTOR LAYERS ON SAPPHIRE SUBSTRATES, AND GALLIUM NITRIDE
SEMICONDUCTOR STRUCTURES FABRICATED THEREBY

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**INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. § 1.56 AND 37 C.F.R. § 1.97**

It is respectfully requested that the documents listed on the attached Form PTO/SB/08A be considered by the Patent and Trademark Office in the above-referenced application and made of record therein. A full text copy of the relevant documents have been previously disclosed in the parent application Ser. No. 09/899,586. This information disclosure statement submitted herewith is being filed within three months of the filing date of the application or date of entry into the national stage of an international application or before the mailing date of a first Office action on the merits, whichever event occurs last.

Respectfully submitted,

By:



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1/23/04
Date

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(Use several sheets if necessary)Applicants:
Gehrke et al.Filing Date:
November 17, 1999GAU:
2812

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